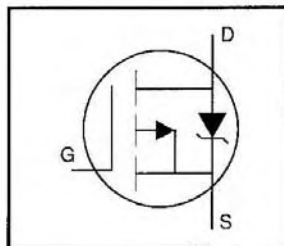


IRFR9220PbF IRFU9220PbF

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Surface Mount (IRFR9220)
- Straight Lead (IRFU9220)
- Available in Tape & Reel
- P-Channel
- Fast Switching
- Lead-Free



$$V_{DSS} = -200V$$

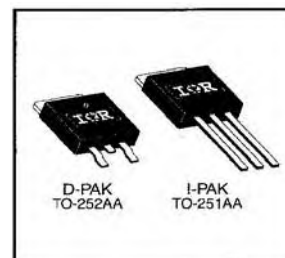
$$R_{DS(on)} = 1.5\Omega$$

$$I_D = -3.6A$$

Description

The HEXFET technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and extreme device ruggedness.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10 V$	-3.6	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10 V$	-2.3	
I_{DM}	Pulsed Drain Current ①	-14	
$P_D @ T_C = 25^\circ C$	Power Dissipation	42	W
$P_D @ T_A = 25^\circ C$	Power Dissipation (PCB Mount)**	2.5	
	Linear Derating Factor	0.33	W/°C
	Linear Derating Factor (PCB Mount)**	0.020	
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	310	mJ
I_{AR}	Avalanche Current ①	-3.6	A
E_{AR}	Repetitive Avalanche Energy ①	4.2	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	260 (1.6mm from case)	

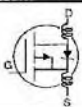
Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	3.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	—	110	

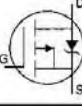
** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-200	—	—	V	$V_{GS}=0V$, $I_D=-250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.22	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D=-1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	1.5	Ω	$V_{GS}=10V$, $I_D=-2.2A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS}=V_{GS}$, $I_D=-250\mu A$
g_{fs}	Forward Transconductance	1.1	—	—	S	$V_{DS}=-50V$, $I_D=-2.2A$ ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	-100	μA	$V_{DS}=-200V$, $V_{GS}=0V$
		—	—	-500		$V_{DS}=-160V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS}=-20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS}=20V$
Q_g	Total Gate Charge	—	—	20	nC	$I_D=-3.9A$
Q_{gs}	Gate-to-Source Charge	—	—	3.3		$V_{DS}=-160V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	11		$V_{GS}=-10V$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	8.8	—	ns	$V_{DD}=-100V$
t_r	Rise Time	—	27	—		$I_D=-3.9A$
$t_{d(off)}$	Turn-Off Delay Time	—	7.3	—		$R_G=18\Omega$
t_f	Fall Time	—	19	—		$R_D=24\Omega$ See Figure 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	340	—	pF	$V_{GS}=0V$
C_{oss}	Output Capacitance	—	110	—		$V_{DS}=-25V$
C_{rss}	Reverse Transfer Capacitance	—	33	—		$f=1.0MHz$ See Figure 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-3.6	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-14		
V_{SD}	Diode Forward Voltage	—	—	-6.3	V	$T_J=25^\circ\text{C}$, $I_S=-3.6A$, $V_{GS}=0V$ ②
t_{rr}	Reverse Recovery Time	—	150	300	ns	$T_J=25^\circ\text{C}$, $I_F=-3.9A$
Q_{rr}	Reverse Recovery Charge	—	0.97	2.0	μC	$di/dt=100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)

② $V_{DD}=-50V$, starting $T_J=25^\circ\text{C}$, $L=35mH$
 $R_G=25\Omega$, $I_{AS}=-3.6A$ (See Figure 12)

③ $I_{SD}\leq 3.9A$, $di/dt\leq 95A/\mu s$, $V_{DD}\leq V_{(BR)DSS}$,
 $T_J\leq 150^\circ\text{C}$

④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

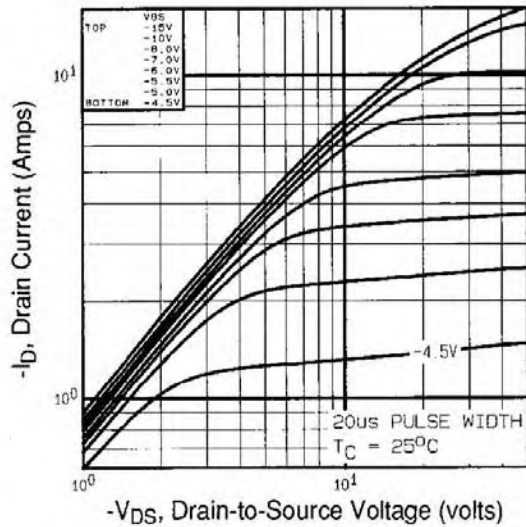


Fig 1. Typical Output Characteristics,
 $T_C = 25^\circ\text{C}$

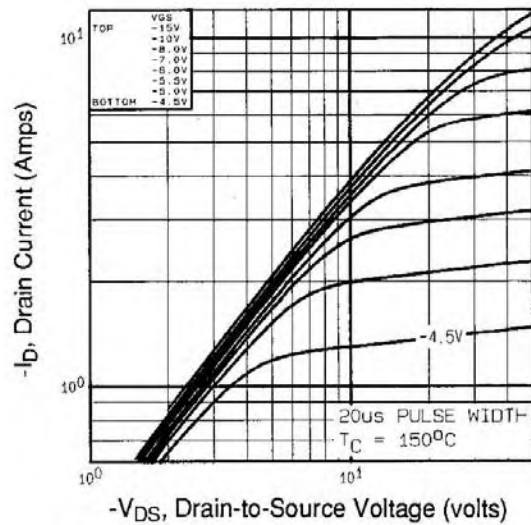


Fig 2. Typical Output Characteristics,
 $T_C = 150^\circ\text{C}$

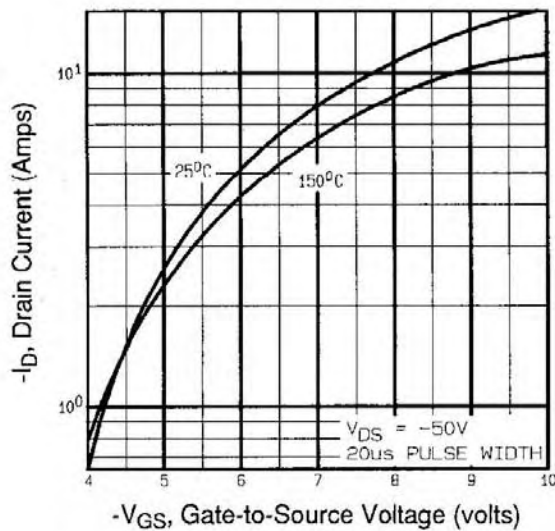


Fig 3. Typical Transfer Characteristics

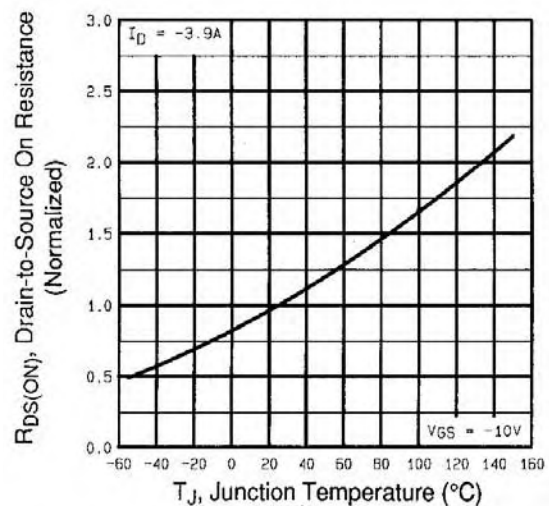


Fig 4. Normalized On-Resistance
Vs. Temperature

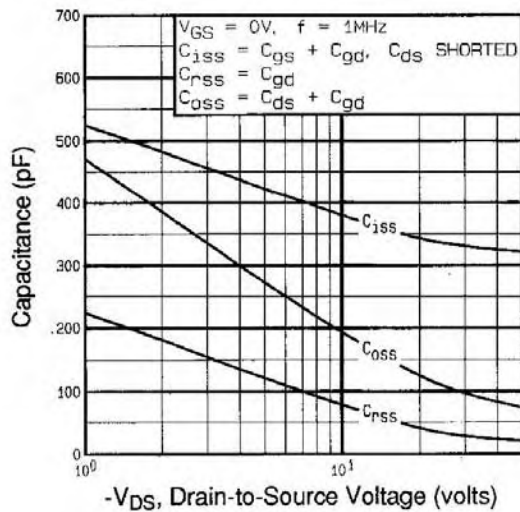


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

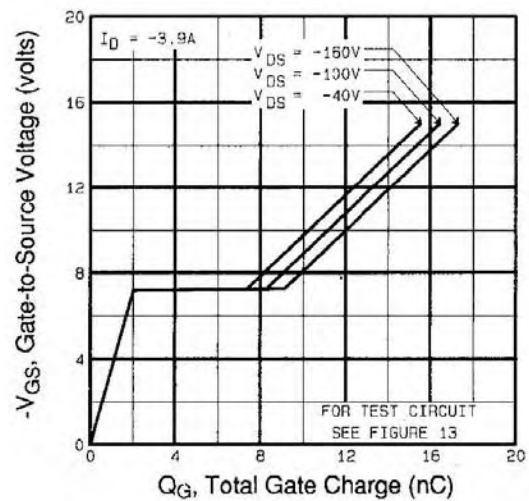


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

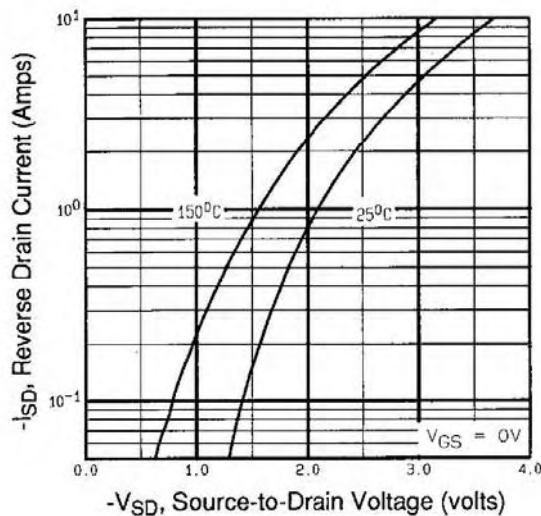


Fig 7. Typical Source-Drain Diode Forward Voltage

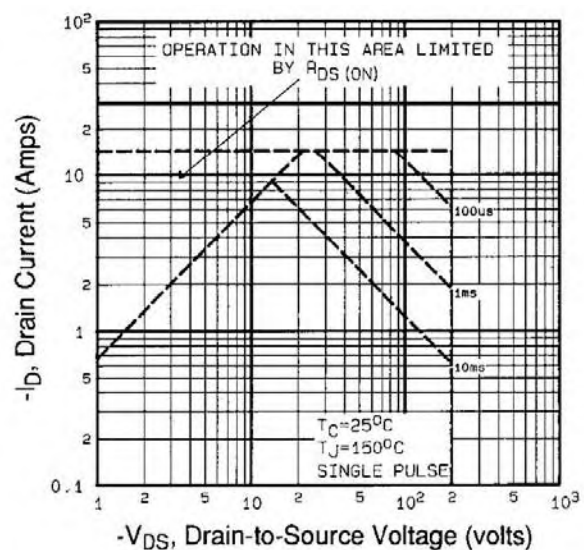


Fig 8. Maximum Safe Operating Area

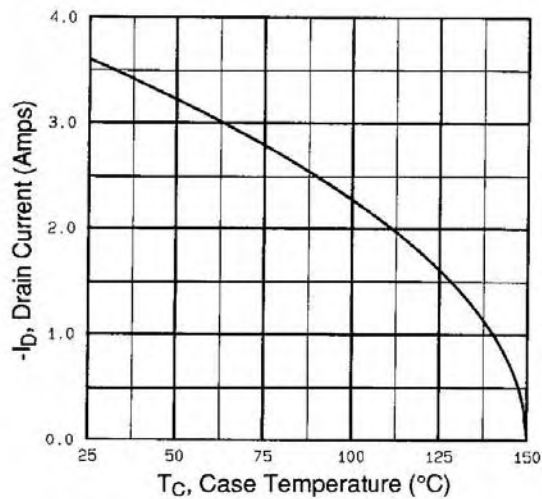


Fig 9. Maximum Drain Current Vs. Case Temperature

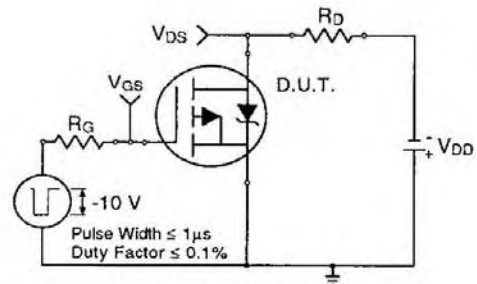


Fig 10a. Switching Time Test Circuit

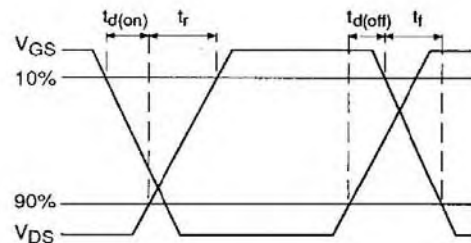


Fig 10b. Switching Time Waveforms

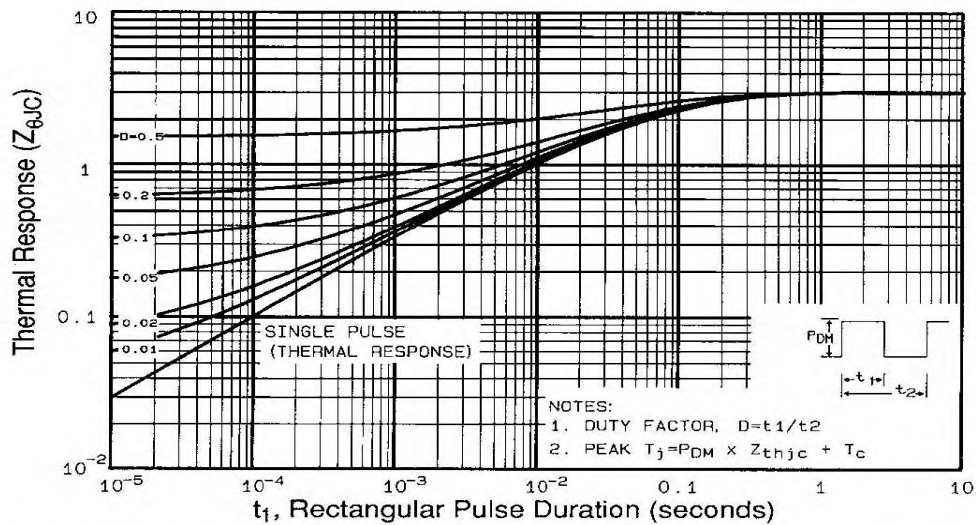


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

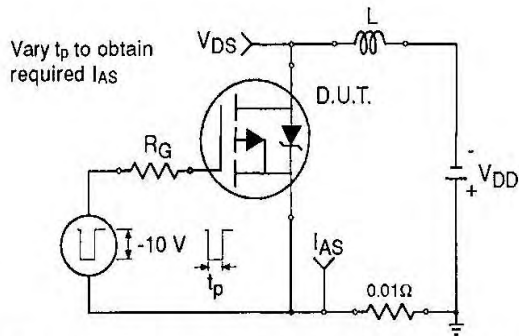


Fig 12a. Unclamped Inductive Test Circuit

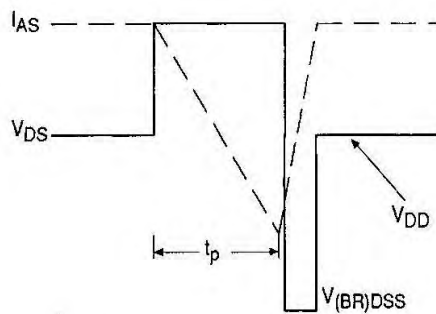


Fig 12b. Unclamped Inductive Waveforms

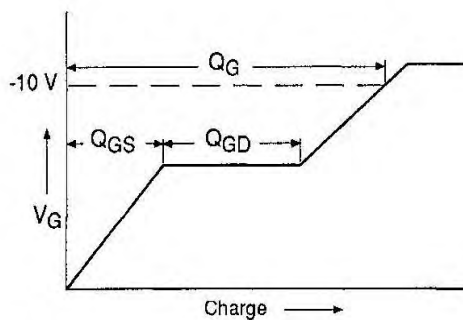


Fig 13a. Basic Gate Charge Waveform

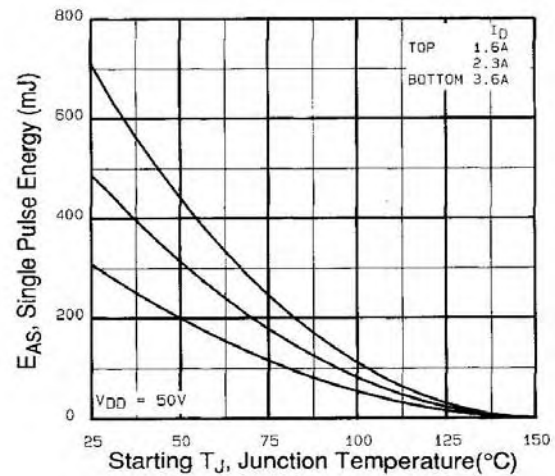


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

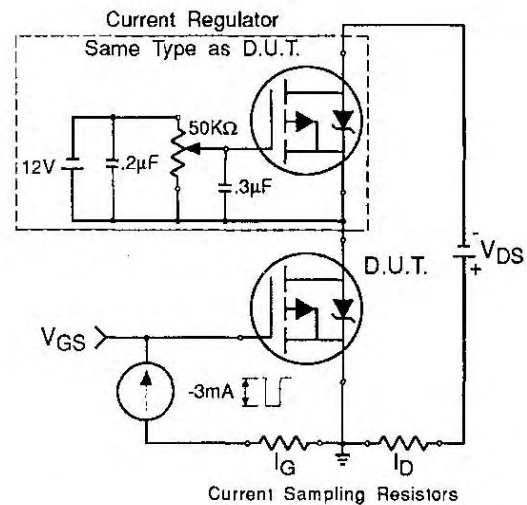
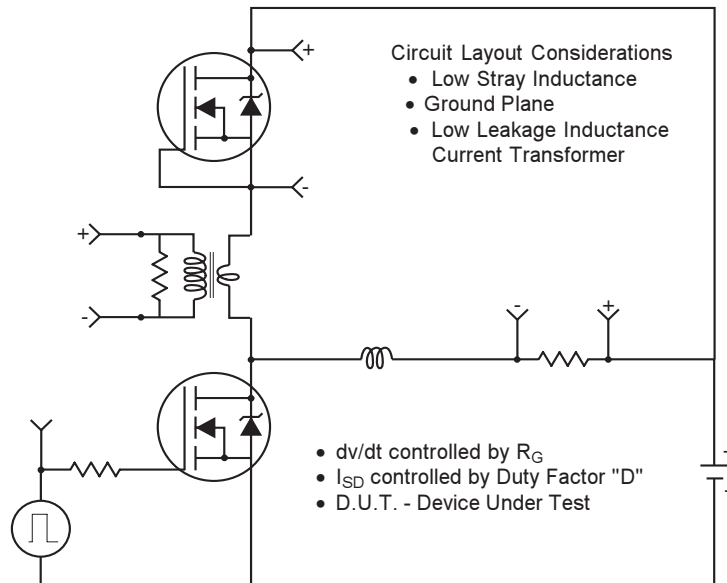


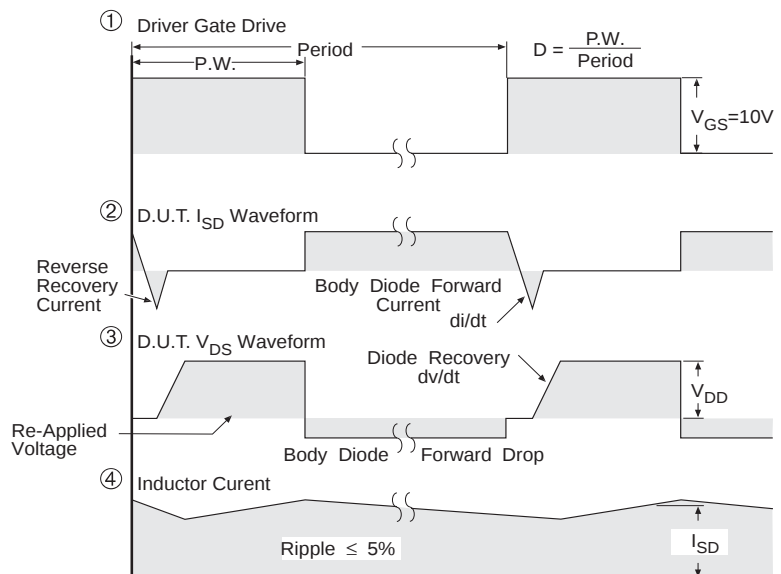
Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements

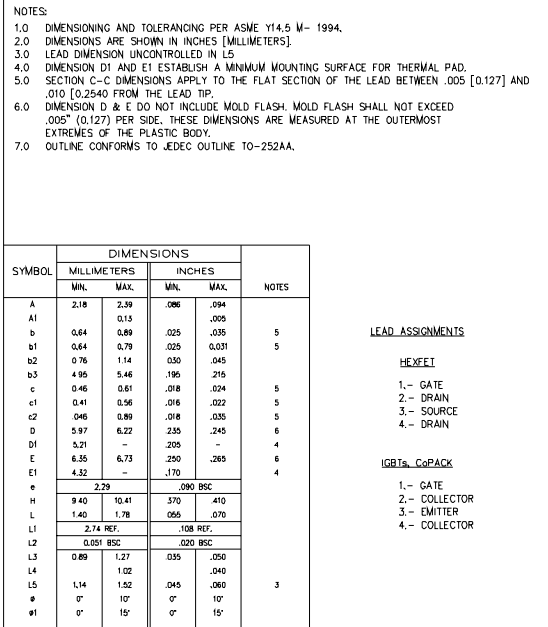


*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 14 For P Channel HEXFETS

International
IOR Rectifier

Dimensions are shown in millimeters (inches)



EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 1999
IN THE ASSEMBLY LINE "A"

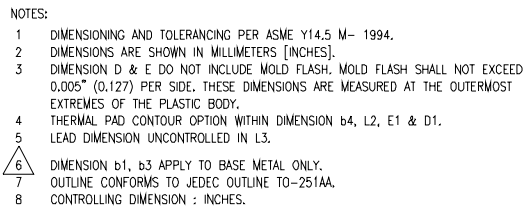
Diagram illustrating the identification marks on a MOSFET package:

- INTERNATIONAL RECTIFIER LOGO**: Points to the IR logo on the package.
- PART NUMBER**: Points to the text "IRFU120" on the package.
- DATE CODE**: Points to the text "12 34" on the package.
- YEAR 9 = 1999**: Points to the first digit of the date code "12".
- WEEK 16**: Points to the second digit of the date code "34".
- LINE A**: Points to the letter "A" on the package.
- ASSEMBLY LOT CODE**: Points to the text "12 34" on the package.

Diagram illustrating the markings on a diode package:

- INTERNATIONAL RECTIFIER LOGO**: Points to the IR logo on the package.
- PART NUMBER**: Points to the part number **IRFU120** on the package.
- DATE CODE**: Points to the date code **P =** on the package.
- ASSEMBLY LOT CODE**: Points to the assembly lot code **12 34** on the package.
- LEGEND**:
 - P =** DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)
 - YEAR 9 = 1999**
 - WEEK 16**
 - A = ASSEMBLY SITE CODE**

Dimensions are shown in millimeters (inches)



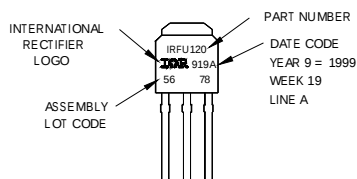
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	—	0.205	—	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	—	0.170	—	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	0"	15'	0"	15'	

HEXFET

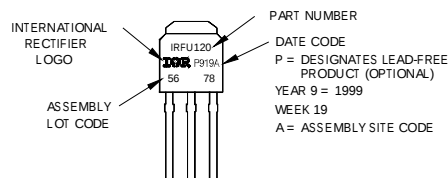
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON VW 19, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line
position indicates "Lead-Free"



OR

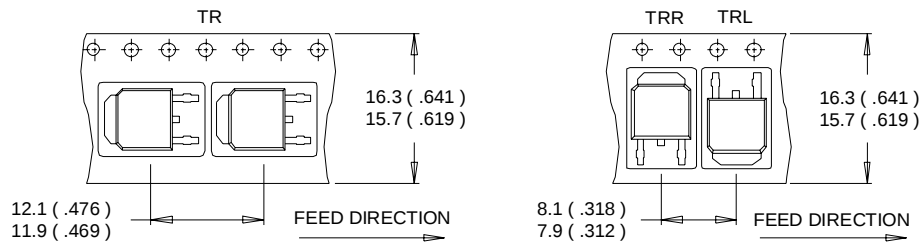


IRFR/U9220PbF

International
IOR Rectifier

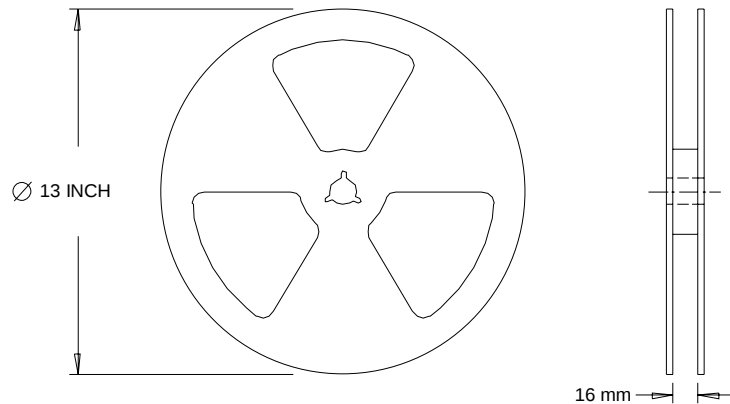
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

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